

Power Amplifier, 2 W 21.15 - 23.65 GHz

Rev. V2

Features

- 24 dB Small Signal Gain
- 41 dBm Third Order Intercept Point (OIP3)
- >2 W Output P1dB
- 35 dBm Saturated Output Power
- Integrated Power Detector
- Bias 1330 mA @ 6 V
- Lead-Free 7 mm Cavity Package
- RoHS* Compliant

Description

The MAAP-011146-STD is a power amplifier assembled in a 7 mm surface mount package with a temperature compensated integrated power detector operating from 21.15 to 23.65 GHz. The circuit provides 24 dB gain, 41 dBm OIP3, 2 W P1dB and 35 dBm saturated output power.

The device includes ESD protection and by-pass capacitors to ease the implementation and volume assembly of the packaged part.

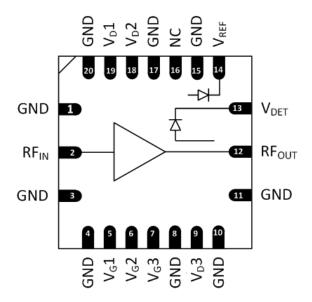
This power amplifier is specifically designed for use in point-to-point radios for cellular backhaul applications in the 23 GHz band.

Ordering Information¹

Part Number	Package
MAAP-011146-STD	Bulk Quantity
MAAP-011146-STR500	500 piece reel
MAAP-011146-001SMB	Sample Board

1. Reference Application Note M513 for reel size information.

Functional Schematic



Pin Configuration²

Pin No.	Function	Pin No.	Function	
1	Ground	11	Ground	
2	RF Input	12	RF Output	
3	Ground	13	Power Detector	
4	Ground	14	Reference	
5	Gate 1 Bias	15	Ground	
6	Gate 2 Bias	16	No Connection	
7	Gate 3 Bias	17	Ground	
8	Ground	18	Drain 2 Bias	
9	Drain 3 Bias	19	Drain 1 Bias	
10	Ground	20	Ground	
		21 ³	Paddle	

- 2. All "No Connection" pins should be grounded.
- 3. The exposed pad centered on the package bottom must be connected to RF, DC and thermal ground.

^{*} Restrictions on Hazardous Substances, European Union Directive 2011/65/EU.



Power Amplifier, 2 W 21.15 - 23.65 GHz

Rev. V2

Electrical Specifications: $V_{DD} = 6 \text{ V}$, $I_{DQ}^{4} = 1330 \text{ mA}$, $T_{A} = +25^{\circ}\text{C}$

Parameter	Units	Min.	Тур.	Max.
Small Signal Gain	dB	21.7	24.0	28.3
P _{SAT}	dBm	34	35	_
Output IP3, +20 dBm SCL	dBm	39.25	41.00	_
Output IP3, +24 dBm SCL	dBm	37.25	39.00	_
P1dB	dBm	_	34	_
Input Return Loss	dB	_	15	_
Output Return Loss	dB	_	10	_
Detector V _{diff} , POUT= +20 dBm	V	0.5	1.1	1.7
Noise Figure	dB	_	6	_
Gain Ripple over frequency	dB	_	2	_
Gate Voltage	V	_	_	-0.60

^{4.} Adjust V_G1 , V_G2 and V_G3 between -1.2 and -0.6 V to achieve specified I_{DQ} ($I_{DQ} = I_D1 + I_D2 + I_D3$). V_G1 , V_G2 and V_G3 are nominally the same voltage.



Power Amplifier, 2 W 21.15 - 23.65 GHz

Rev. V2

Absolute Maximum Ratings^{5,6,7}

Parameter	Rating		
Input Power	18 dBm		
Drain Voltage (V _D 1,2,3)	7 V		
Gate Voltage (V _G 1,2,3)	-3 V		
Drain to Gate Voltage (V _D -V _G)	10 V		
Current ($I_{DQ} = I_D 1 + I_D 2 + I_D 3$)	2000 mA		
Detector Pin	6 V		
Detector Reference Pin	6 V		
Detector Pout	35 dBm		
Junction Temperature	+175°C		
Storage Temperature	-65°C to +150°C		

- 5. Exceeding any one or combination of these limits may cause permanent damage to this device.
- MACOM does not recommend sustained operation near these survivability limits.
- Operating at nominal conditions with T_J ≤ +150°C will ensure MTTF > 1 x 10⁶ hours.

Maximum Operating Ratings^{8,9}

Parameter	Rating
PDISS	11.2 W
Junction Temperature	+150°C
Operating Temperature	-40°C to +85°C

- Channel temperature directly affects device MTTF. Chanel temperature should be kept as low as possible to maximize lifetime. Thermal resistance, Ojc, is 5.8 °C/W.
- 9. For saturated performance, it is recommended that the sum of (2V_{DD} + abs (V_{GG})) < 15 V.

Handling Procedures

Please observe the following precautions to avoid damage:

Static Sensitivity

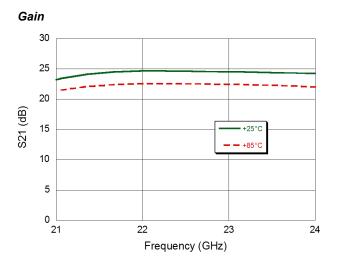
These electronic devices are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these CDM class 2, HBM class 1B devices.



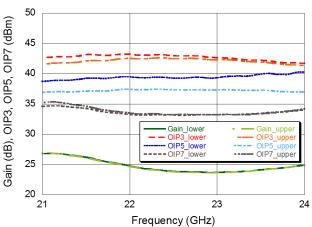
Power Amplifier, 2 W 21.15 - 23.65 GHz

Rev. V2

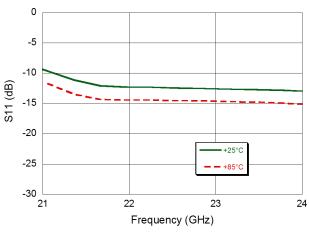
Typical Performance Curves: 8 W Quiescent Bias, V_D = 6 V



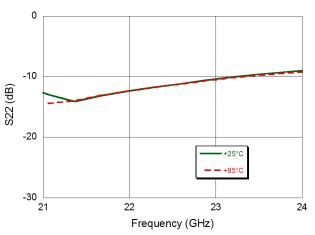
Gain, OIP3, OIP5, OIP7 @ P_{IN} = -6 dBm per tone

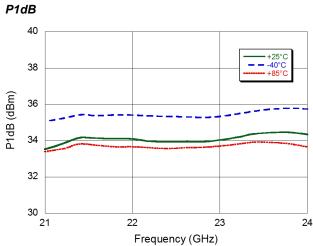


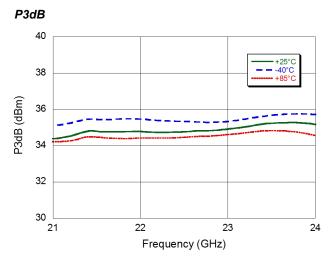
Input Return Loss



Output Return Loss





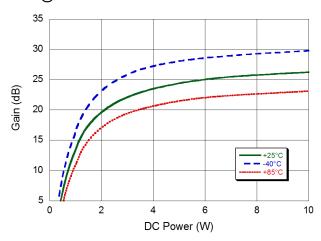




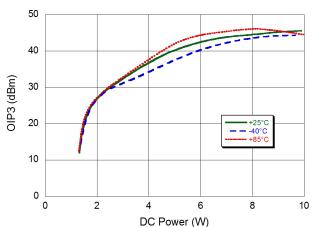
Rev. V2

Typical Performance Curves: $V_D = 6 V$

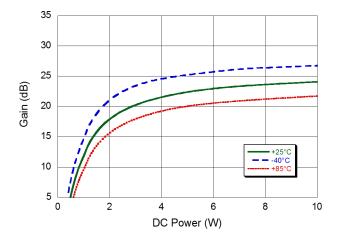
Gain @ 21.2 GHz



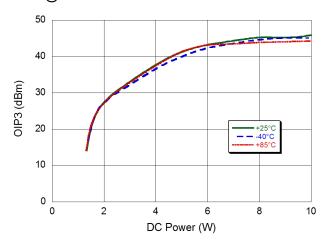
OIP3 @ 21.2 GHz



Gain @ 22.2 GHz



OIP3 @ 22.2 GHz

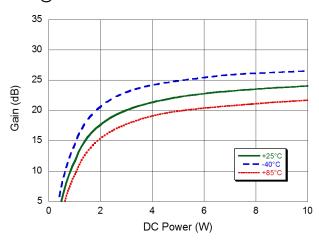




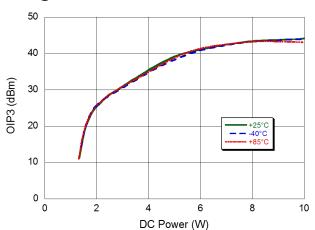
Rev. V2

Typical Performance Curves: $V_D = 6 V$

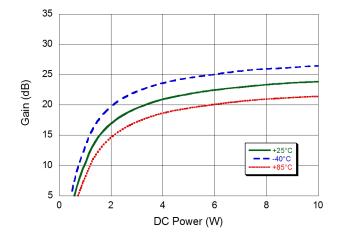
Gain @ 22.7 GHz



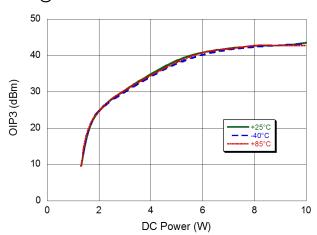
OIP3 @ 22.7 GHz



Gain @ 23.7 GHz



OIP3 @ 23.7 GHz

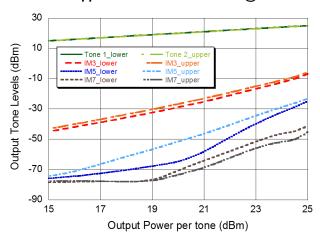




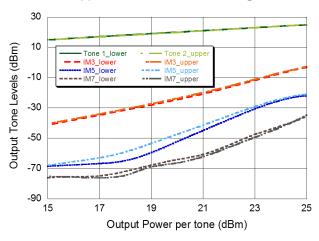
Rev. V2

Typical Performance Curves: 8 W Quiescent Bias, V_D = 6 V

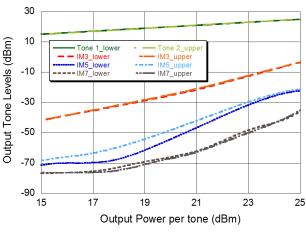
Lower and Upper Intermodulation Tones @ 21.2 GHz



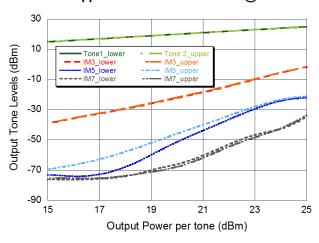
Lower and Upper Intermodulation Tones @ 22.2 GHz



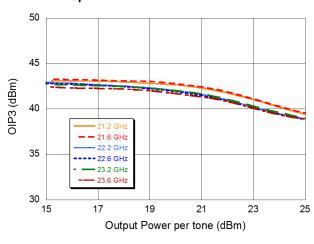
Lower and Upper Intermodulation Tones @ 22.7 GHz



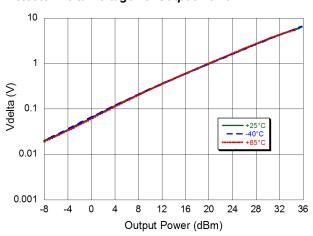
Lower and Upper Intermodulation Tones @ 23.7 GHz



OIP3 vs. Output Power



Detector Delta Voltage vs. Output Power





Rev. V2

Biasing -

All gates should be pinched-off (V_G < -2 V) before applying drain voltage (V_D = 6 V). Then the gate voltages can be increased until the desired quiescent drain current is reached in each stage. The recommended quiescent bias is V_D = 6 V, I_D1 = 190 mA, I_D2 = 380 mA and I_D3 = 762 mA. The performance in this datasheet has been measured with fixed gate voltage and no drain current regulation under large signal operation. It is also possible to regulate the drain current dynamically, to limit the DC power dissipation under RF drive. To turn off the device, the turn on bias sequence should be followed in reverse.

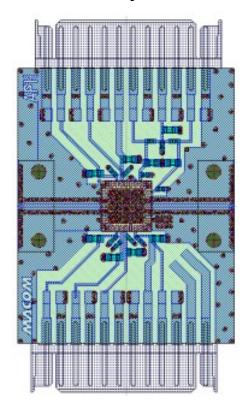
Bias Arrangement -

Each DC pin ($V_D1,2,3$ and $V_G1,2,3$) needs to have bypass capacitance (120 pF and 10 nF) mounted as close to the MMIC as possible.

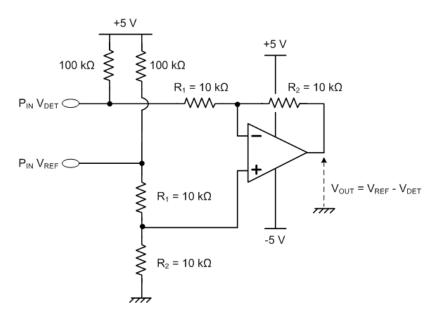
Power Detector -

As shown in the schematic below, the power detector is implemented by providing +5 V bias and measuring the difference in output voltage with standard op-amp in a differential mode configuration.

Evaluation Board Layout



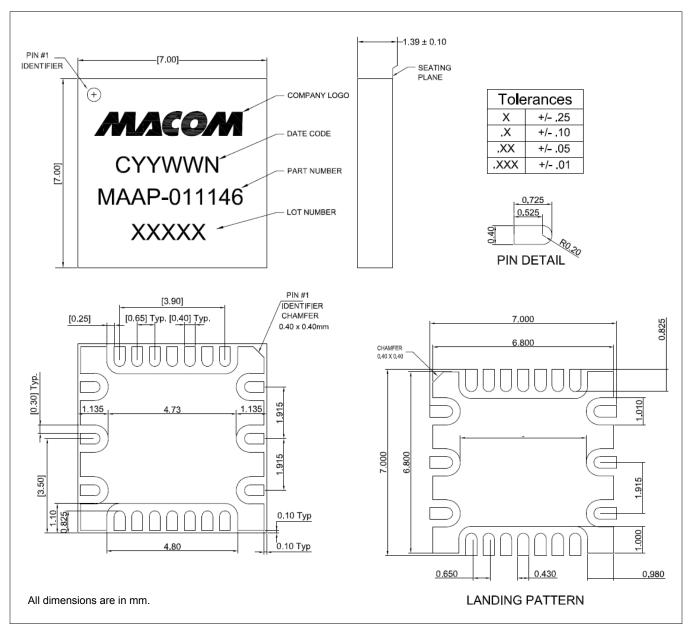
Application Schematic





Rev. V2

Package Outline Drawing and Recommended Land Pattern[†]



 $^{^{\}dagger}$ Meets JEDEC moisture sensitivity level 3 requirements.



Power Amplifier, 2 W 21.15 - 23.65 GHz

Rev. V2

M/A-COM Technology Solutions Inc. All rights reserved.

Information in this document is provided in connection with M/A-COM Technology Solutions Inc ("MACOM") products. These materials are provided by MACOM as a service to its customers and may be used for informational purposes only. Except as provided in MACOM's Terms and Conditions of Sale for such products or in any separate agreement related to this document, MACOM assumes no liability whatsoever. MACOM assumes no responsibility for errors or omissions in these materials. MACOM may make changes to specifications and product descriptions at any time, without notice. MACOM makes no commitment to update the information and shall have no responsibility whatsoever for conflicts or incompatibilities arising from future changes to its specifications and product descriptions. No license, express or implied, by estoppels or otherwise, to any intellectual property rights is granted by this document.

THESE MATERIALS ARE PROVIDED "AS IS" WITHOUT WARRANTY OF ANY KIND, EITHER EXPRESS OR IMPLIED, RELATING TO SALE AND/OR USE OF MACOM PRODUCTS INCLUDING LIABILITY OR WARRANTIES RELATING TO FITNESS FOR A PARTICULAR PURPOSE, CONSEQUENTIAL OR INCIDENTAL DAMAGES, MERCHANTABILITY, OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT. MACOM FURTHER DOES NOT WARRANT THE ACCURACY OR COMPLETENESS OF THE INFORMATION, TEXT, GRAPHICS OR OTHER ITEMS CONTAINED WITHIN THESE MATERIALS. MACOM SHALL NOT BE LIABLE FOR ANY SPECIAL, INDIRECT, INCIDENTAL, OR CONSEQUENTIAL DAMAGES, INCLUDING WITHOUT LIMITATION, LOST REVENUES OR LOST PROFITS, WHICH MAY RESULT FROM THE USE OF THESE MATERIALS.

MACOM products are not intended for use in medical, lifesaving or life sustaining applications. MACOM customers using or selling MACOM products for use in such applications do so at their own risk and agree to fully indemnify MACOM for any damages resulting from such improper use or sale.